



STU7NB100

N - CHANNEL 1000V - 1.2Ω - 7.3A - Max220 PowerMESH™ MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STU7NB100	1000 V	< 1.5 Ω	7.3 A

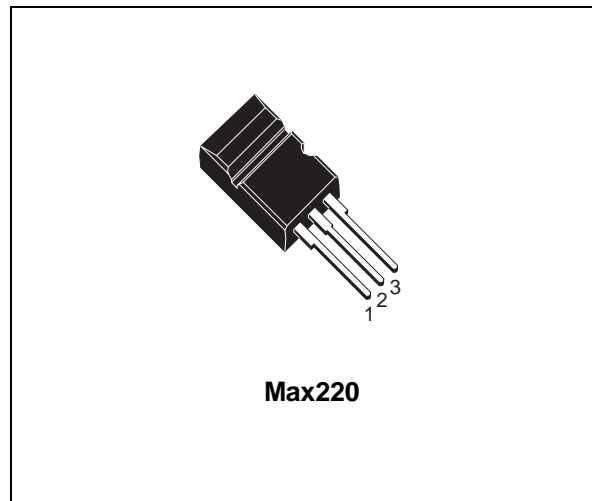
- TYPICAL R_{DS(on)} = 1.2 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- GATE CHARGE MINIMIZED
- REDUCED VOLTAGE SPREAD

DESCRIPTION

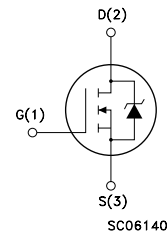
Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY AND MOTOR DRIVE



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	1000	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	1000	V
V _{GS}	Gate-source Voltage	± 30	V
I _D	Drain Current (continuous) at T _c = 25 °C	7.3	A
I _D	Drain Current (continuous) at T _c = 100 °C	4.7	A
I _{DM} (●)	Drain Current (pulsed)	29	A
P _{tot}	Total Dissipation at T _c = 25 °C	160	W
	Derating Factor	1.28	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 7.3 A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.78	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	7.3	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	600	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	1000			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 50	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 4 A		1.2	1.5	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	7.3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 4 A		8.9		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		2900		pF
C _{oss}	Output Capacitance			275		pF
C _{rss}	Reverse Transfer Capacitance			27		pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 500\text{ V}$ $I_D = 3.5\text{ A}$		32		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		13		ns
Q_g	Total Gate Charge	$V_{DD} = 800\text{ V}$ $I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}$		68	95	nC
Q_{gs}	Gate-Source Charge			16		nC
Q_{gd}	Gate-Drain Charge			31		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 800\text{ V}$ $I_D = 7\text{ A}$		32		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		32		ns
t_c	Cross-over Time			40		ns

SOURCE DRAIN DIODE

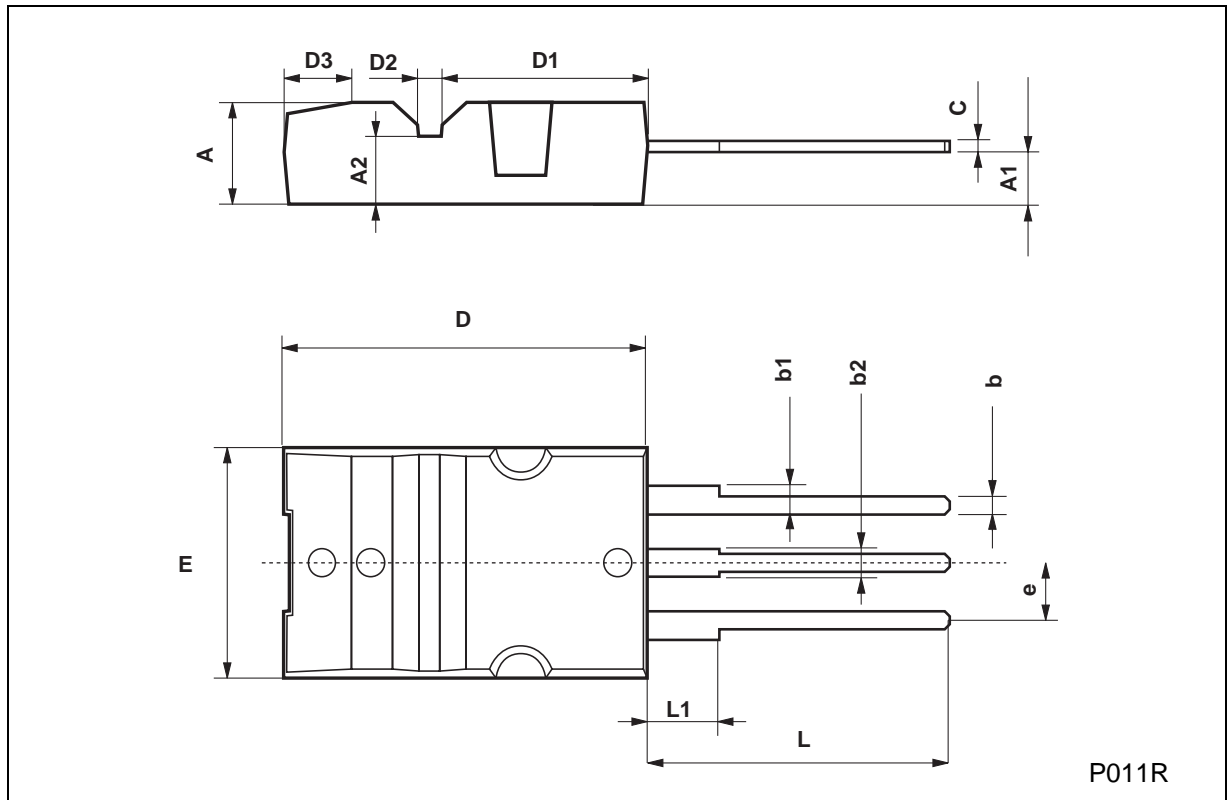
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				7.3	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				29	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 7.3\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		1000		ns
Q_{rr}	Reverse Recovery Charge			11		μC
I_{RRM}	Reverse Recovery Current			21		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Max220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.2		2.4	0.087		0.094
A2	2.9		3.1	0.114		0.122
b	0.7		0.93	0.027		0.036
b1	1.25		1.4	0.049		0.055
b2	1.2		1.38	0.047		0.054
c	0.45		0.6		0.18	0.023
D	15.9		16.3		0.626	0.641
D1	9		9.35	0.354		0.368
D2	0.8		1.2	0.031		0.047
D3	2.8		3.2	0.110		0.126
e	2.44		2.64	0.096		0.104
E	10.05		10.35	0.396		0.407
L	13.2		13.6	0.520		0.535
L1	3		3.4	0.118		0.133



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